## **Supporting Information**

## Role of Water in Suppressing Recombination Pathways in CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> Perovskite Solar Cells

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## Results

X-ray Diffraction pattern

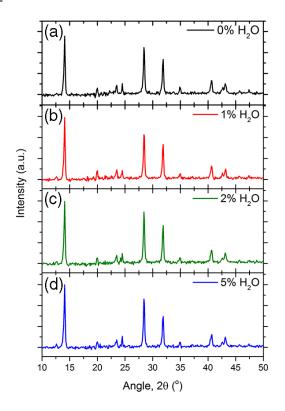
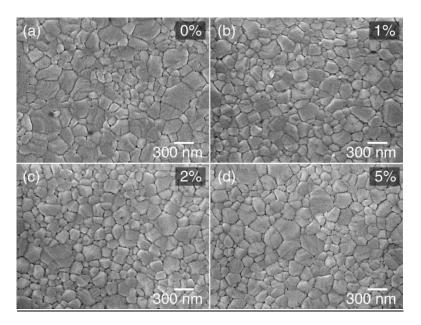
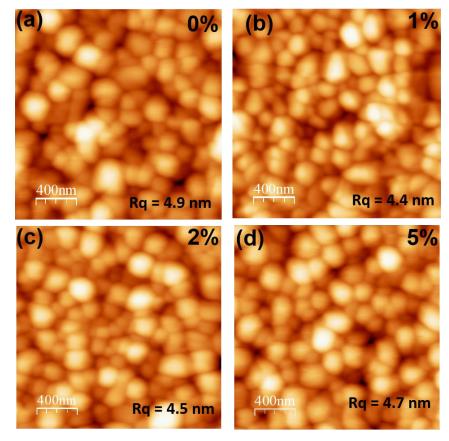


Figure S1. X-ray diffraction spectra of the different samples with varying H<sub>2</sub>O additive concentrations: (a) 0%, (b) 1%, (c) 2% and (d) 5 vol% H<sub>2</sub>O.

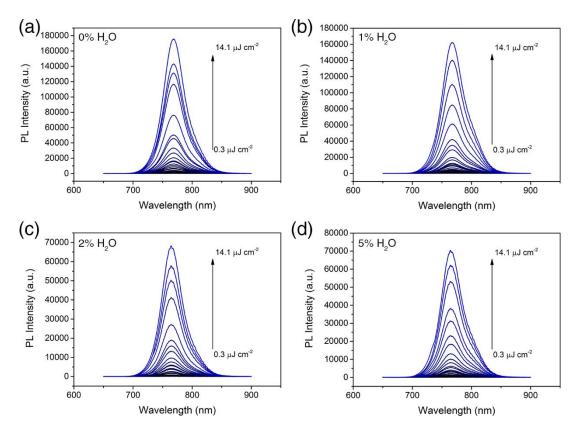
Scanning electron microscopy images



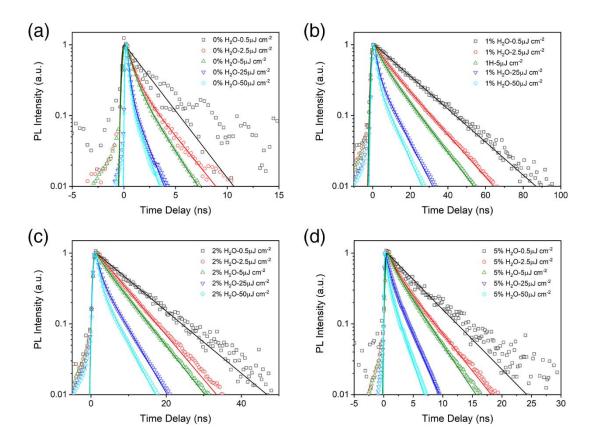
**Figure S2.**SEM images of perovskite films prepared from solutions with varying water additive concentration (a) 0%, (b) 1%, (c) 2% and (d) 5 vol% H<sub>2</sub>O; 1% indicates perovskite solution with 1 vol% H<sub>2</sub>O additive.



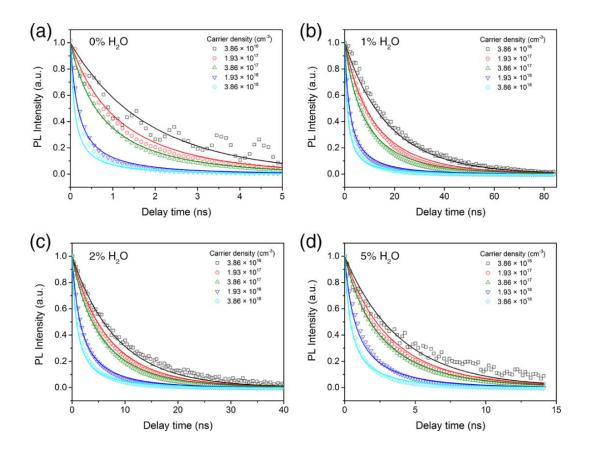
**Figure S3:** AFM images  $(2 \ \mu m \times 2 \ \mu m)$  of perovskite films prepared from solutions with varying water additive concentration with root-mean-square roughnesses of the various samples: (a) Rq<sub>0%</sub> = 4.9 nm, (b) Rq<sub>1%</sub> = 4.4 nm, (c) Rq<sub>2%</sub> = 4.5 nm and (d) Rq<sub>5%</sub> = 4.7 nm for the varying vol% H<sub>2</sub>O-added perovskite films.



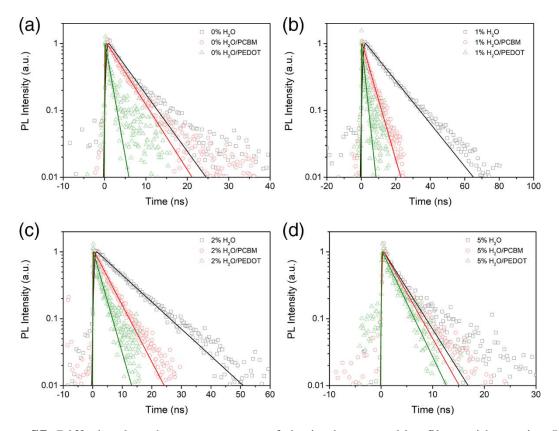
**Figure S4.** Power-dependent photoluminescence (PL) measured in the low fluence regime to extract trap densities in the perovskite films with varying H<sub>2</sub>O additive concentrations: (a) 0%, (b) 1%, (c) 2% and (d) 5 vol% H<sub>2</sub>O.



**Figure S5.** Power dependent time-resolved PL (TRPL) traces fitted with mono- or biexponential decay functions to extract the PL lifetimes and their associated amplitudes in the perovskite films with varying H<sub>2</sub>O additive concentrations: (a) 0%, (b) 1%, (c) 2% and (d) 5 vol% H<sub>2</sub>O.



**Figure S6.** Power dependent TRPL traces fitted with the recombination rate equation (see main text) to extract the monomolecular and bimolecular recombination rate constants in the perovskite films with varying H<sub>2</sub>O additive concentrations: (a) 0%, (b) 1%, (c) 2% and (d) 5 vol% H<sub>2</sub>O.



**Figure S7.** Diffusion length measurements of the in the perovskite films with varying H<sub>2</sub>O additive concentrations: (a) 0%, (b) 1%, (c) 2% and (d) 5 vol% H<sub>2</sub>O with the respective quencher (black: neat film, red: PCBM layer, green: PEDOT layer) measured at a fluence of  $0.5 \,\mu J \, \text{cm}^{-2}$ . Symbols are the data obtained from PL measurements, solid lines are exponential fits.

**Trap density calculation:** Initial photogenerated carrier density in different perovskite films were estimated using Plank Equation ( $\alpha E = \frac{nhc}{\lambda}$ ) (Equation S1), where  $\alpha$  is the absorption coefficient at 600 (=  $\lambda$ ) nm while *E*, *n*, *h*, *c* are excitation pump fluence, charge carrier density, plank constant and light velocity, respectively.  $\alpha$  is calculated using equation  $\alpha = I/L$  (Equation S2) where *I* is the absolute absorption intensity at 600 nm and *L* represents the film thickness (~ 275 nm). In order to estimate the defects density, the integrated steady state PL intensity for the different perovskite films was fitted with the model:

$$n_c(0) = \sum n_{TP}(0)(1 - e^{-k_1 I_{PL}}) + k_2 I_{PL}$$
 Equation S3

where  $n_c(0)$  and  $n_{TP}$  represent photogenerated charge carrier density and trap density, respectively while  $k_1$ ,  $k_2$  are the constants.

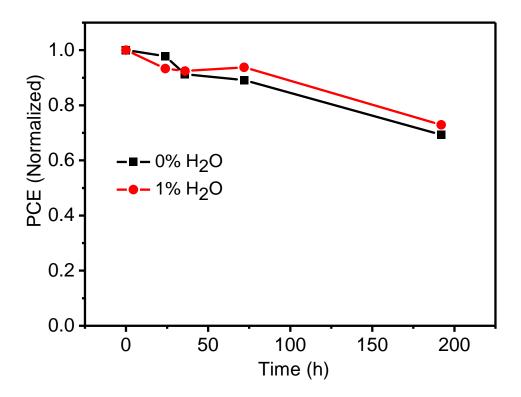


Figure S8: Comparative study of device degradation of 0% and 1% H<sub>2</sub>O added solar cell devices.